

Amendments to the Claims:

The following claims will replace all prior versions of the claims in this application (in the unlikely event that no claims follow herein, the previously pending claims will remain):

1. (Currently Amended) A method of forming a metal line in a semiconductor device, comprising ~~the steps of:~~

(a) sequentially forming a first interlayer insulation film, an etch-stopping layer, and a second interlayer insulation film on a semiconductor substrate having a predetermined semiconductor structural layer;

(b) forming a contact hole which partially exposes the semiconductor structural layer by performing an etching process using an etching mask for the contact hole;

(c) forming a metal plug to bury the contact hole;

(d) sequentially forming an anti-diffusion film and a third interlayer insulation film on ~~the whole structure~~ semiconductor device including the metal plug;

(e) performing an etching process using an etching mask for a trench to form the trench in such a way that the second interlayer insulation film is over-etched by using the etch-stopping layer as an etching barrier; and

(f) forming a metal line to bury the trench.

2. (Original) The method of claim 1, wherein the etch-stopping layer is composed of SiC, SiN, or SiON.

3. (Original) The method of claim 1, wherein the first interlayer insulation film and the second interlayer insulation film are formed by depositing BPSG, PSG, USG, or FSG, or by a film in which fluorine, hydrogen, boron, or phosphorous is locally diffused into SiO or SiO₂ in a substitutional or interstitial manner.

4. (Currently Amended) The method of claim 1, wherein the etching process in the step (b) is performed by using a C_xH_yF_z gas (wherein x is any natural number, y is 0 or any natural number, and z are is 0 or any natural number, and wherein both y and z do not become 0 simultaneously) as a main etchant gas and an inert gaseous atom or a molecule of O₂, N₂, SF₆, Ar, or He as an additive gas.